

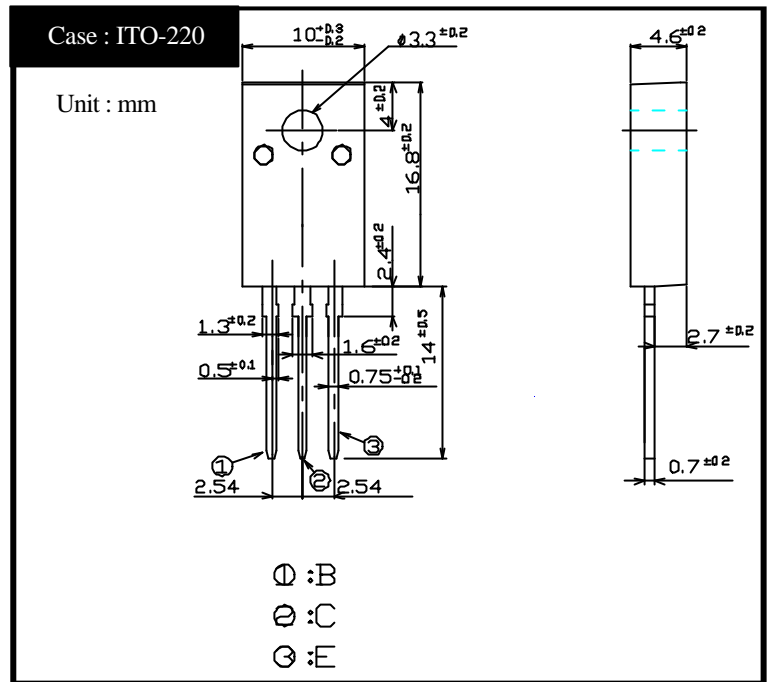
SHINDENGEN

Darlington Transistor

2SB1282
(TP4J10)

± 4A PNP

OUTLINE DIMENSIONS



RATINGS

Absolute Maximum Ratings

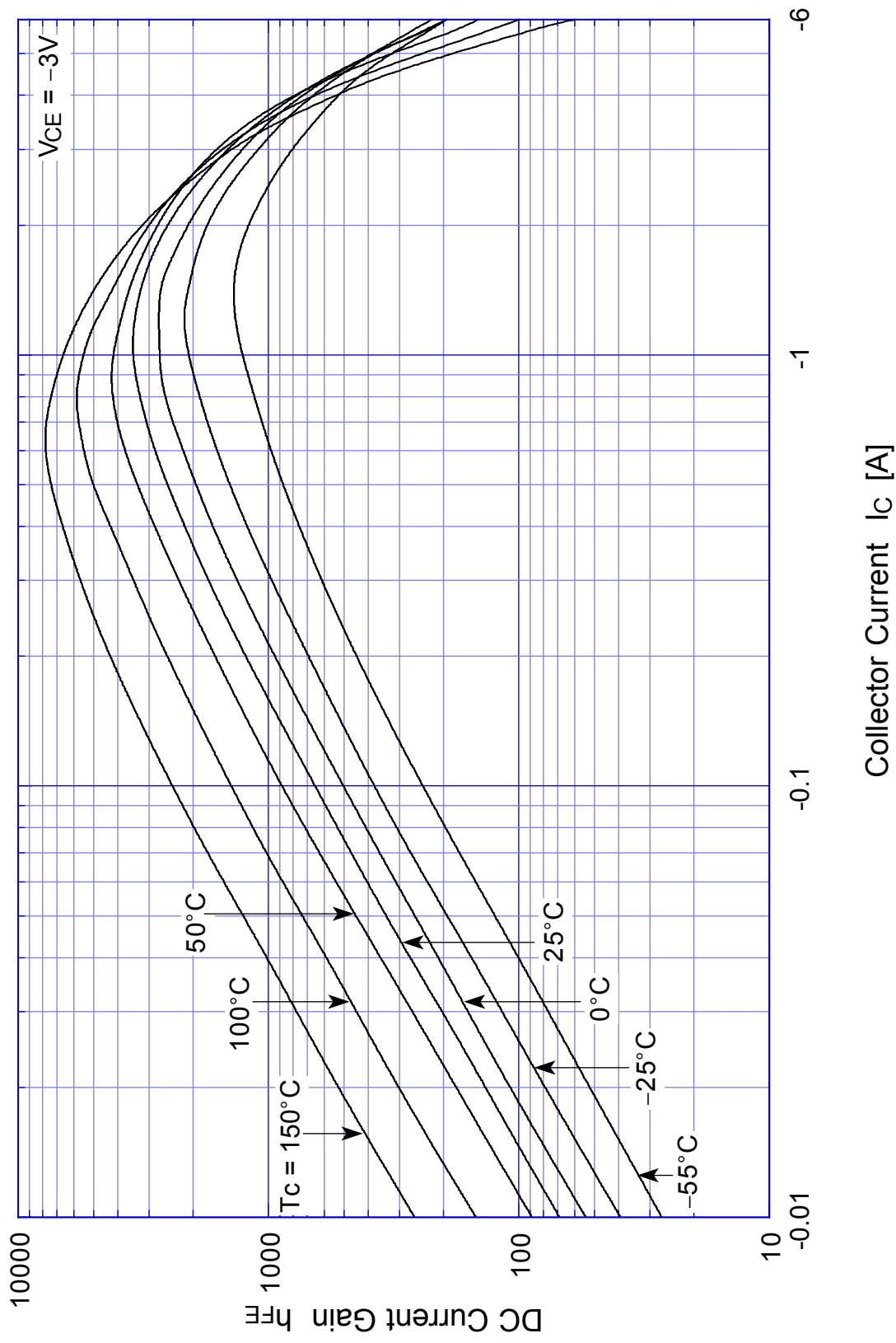
Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T _{stg}		-55 ~ +150	
Junction Temperature	T _j		+150	
Collector to Base Voltage	V _{CB0}		-100	V
Collector to Emitter Voltage	V _{CEO}		-100	V
Emitter to Base Voltage	V _{EBO}		-7	V
Collector Current DC	I _C		-+4	A
Collector Current Peak	I _{CP}		-+6	A
Base Current DC	I _B		-0.3	A
Base Current Peak	I _{BP}		-0.5	A
Total Transistor Dissipation	P _T	T _c = 25	25	W
Dielectric Strength	V _{dis}	Terminals to case AC 1 minute	2	kV
Mounting Torque	TOR	(Recommended torque : 0.3N·m)	0.5	N·m

Electrical Characteristics (T_c=25)

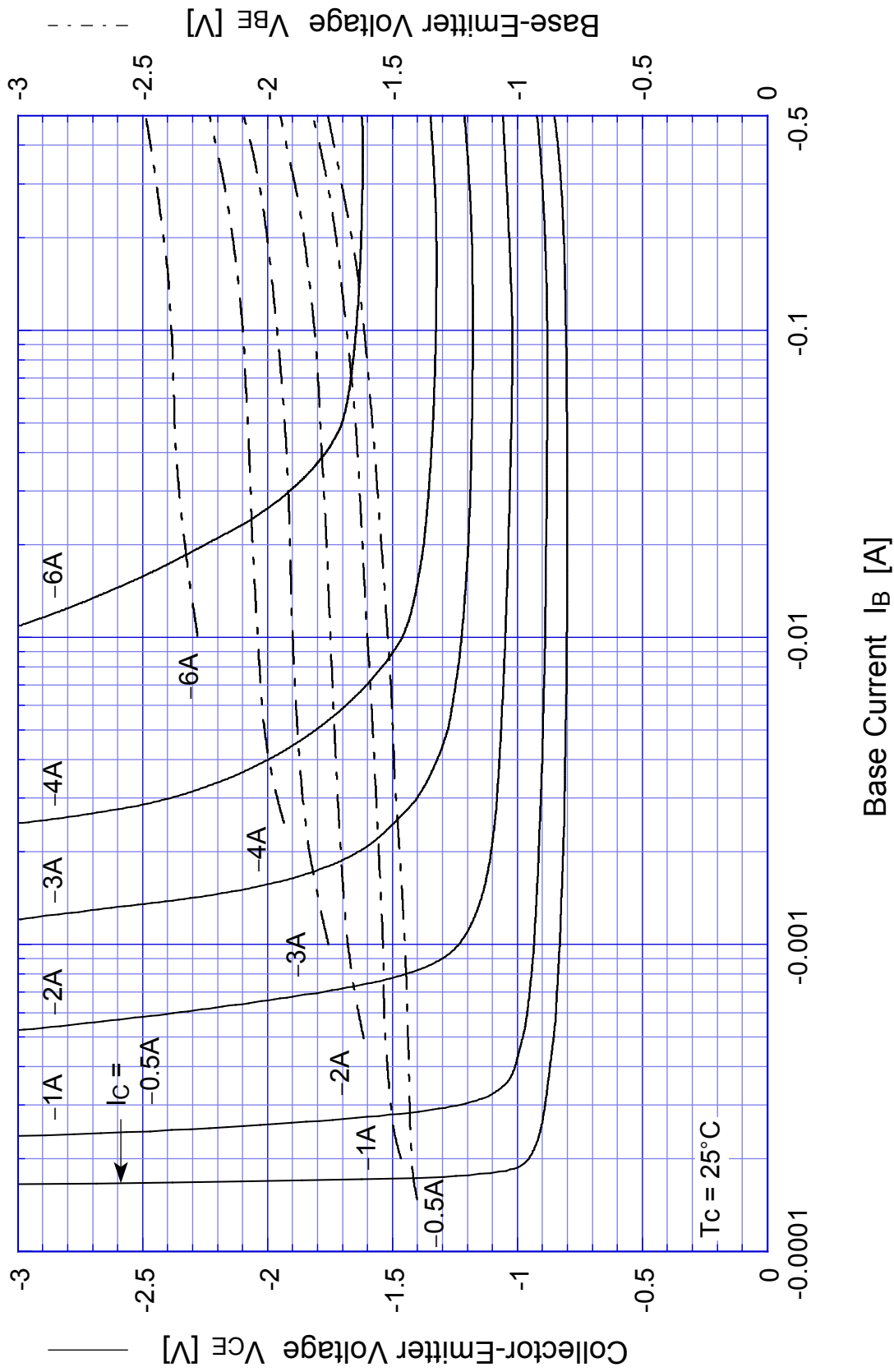
Item	Symbol	Conditions	Ratings	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} = -100V	Max -0.1	mA
	I _{CEO}	V _{CE} = -100V	Max -0.1	
Emitter Cutoff Current	I _{EBO}	V _{EB} = -7V	Max -5	mA
DC Current Gain	h _{FE}	V _{CE} = -3V, I _C = -1A	Min 1,500	
			Max 15,000	
Collector to Emitter Saturation Voltage	V _{CE(sat)}	I _C = -1A	Max -1.5	V
Base to Emitter Saturation Voltage	V _{BE(sat)}	I _B = -2mA	Max -2.0	V
Thermal Resistance	θ _{jc}	Junction to case	Max 5.0	/W
Transition Frequency	f _T	V _{CE} = 10V, I _C = -0.4A	TYP 20	MHz
Turn on Time	t _{on}	I _C = -1A I _{B1} = I _{B2} = -2mA R _L = 25 V _{BB2} = -4V	Max 1	μs
Storage Time	t _s		Max 4	
Fall Time	t _f		Max 2	

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$h_{FE} - I_C$

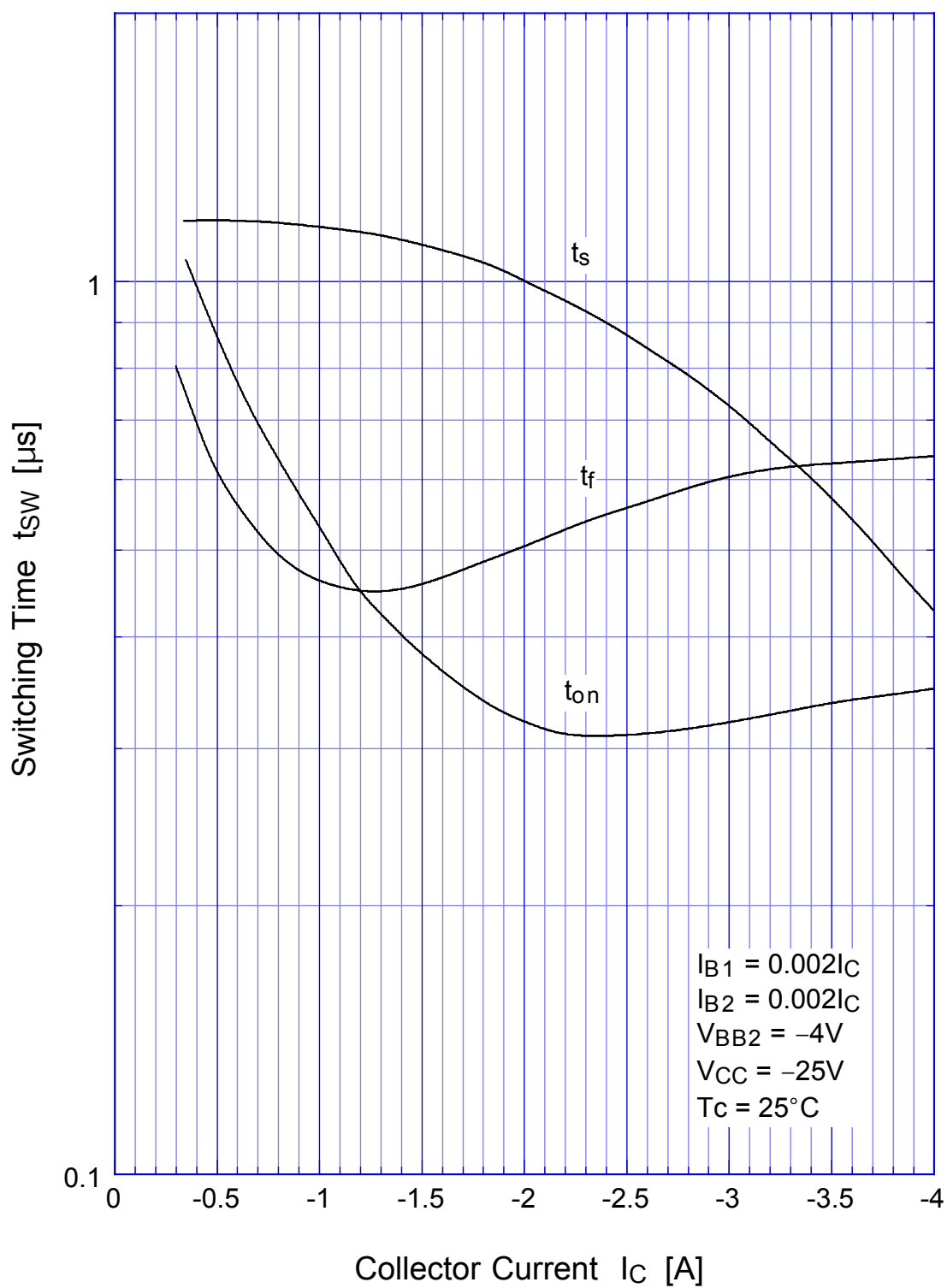


2SB1282 Saturation Voltage



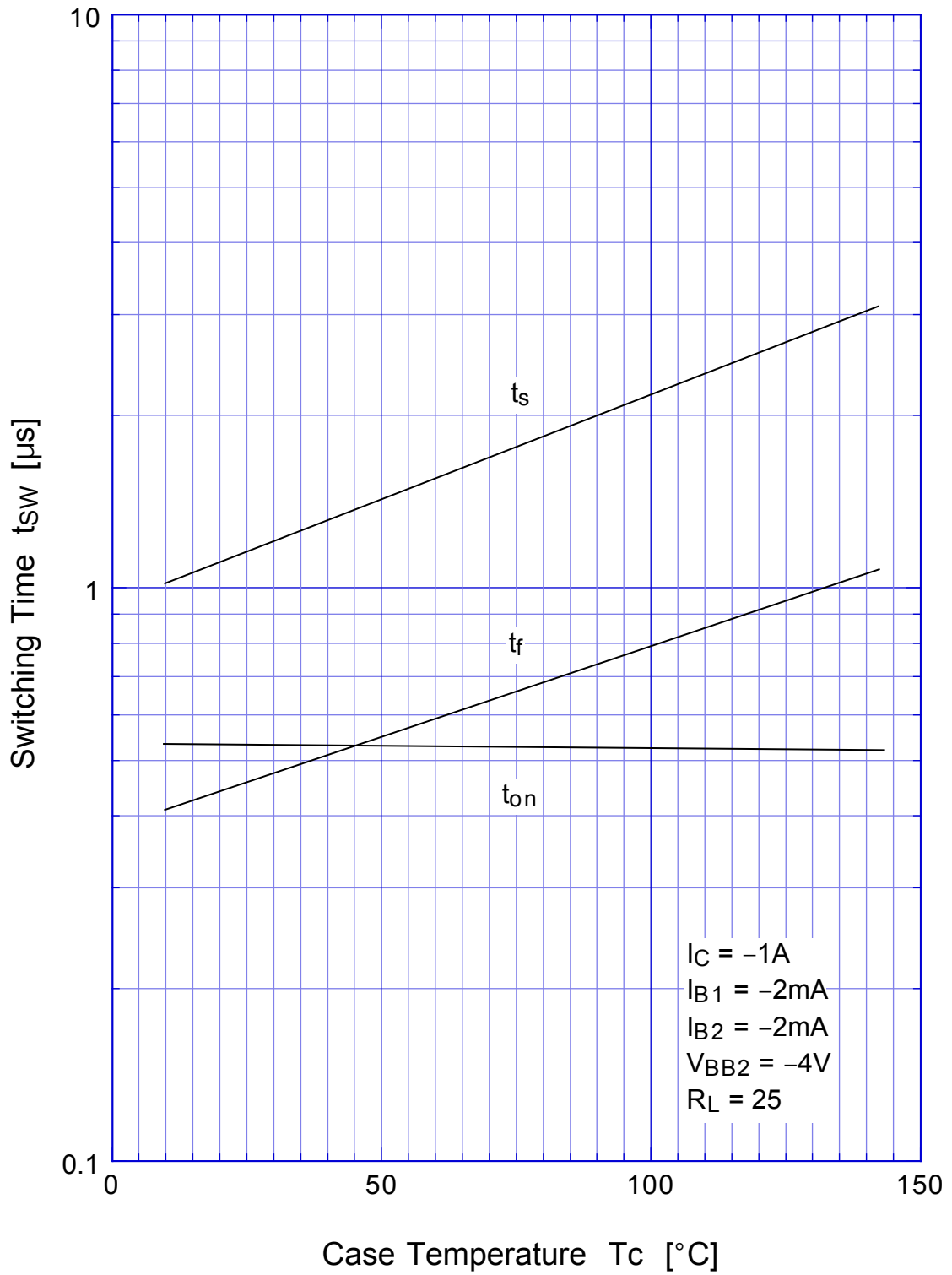
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Switching Time - I_C

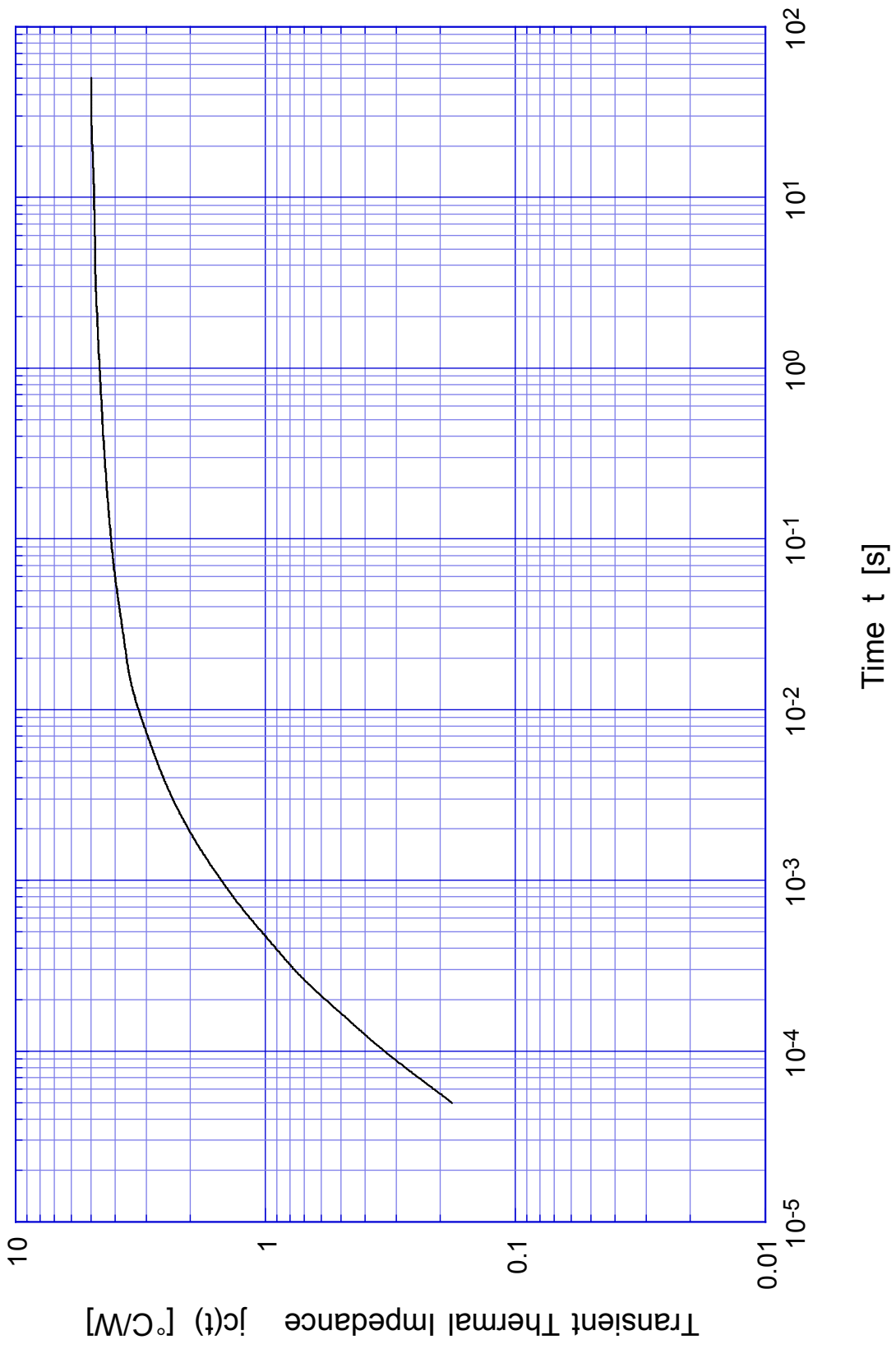


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Switching Time - Tc

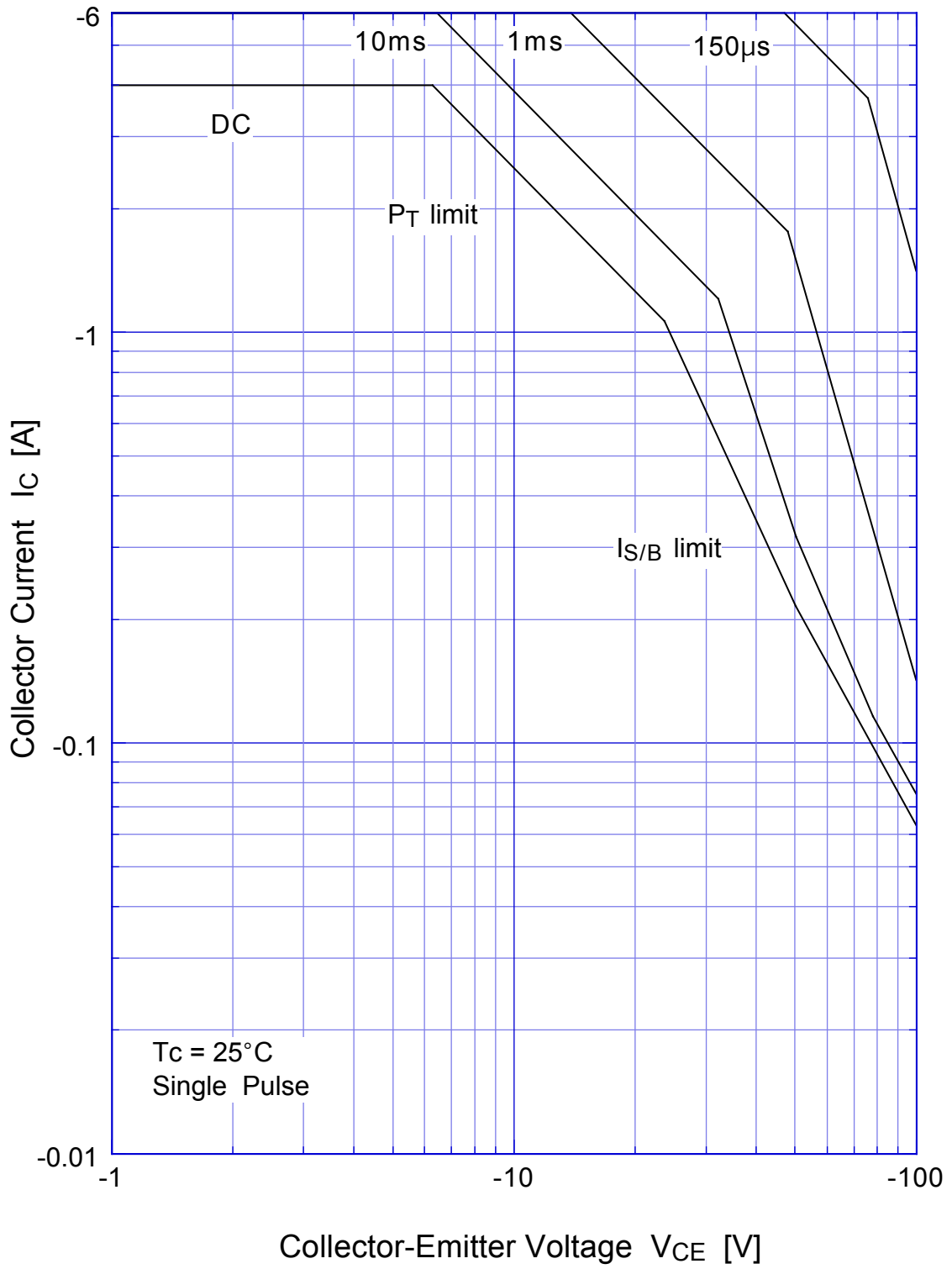


2SB1282 Transient Thermal Impedance



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Forward Bias SOA



2SB1282 Collector Current Derating



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Reverse Bias SOA

